



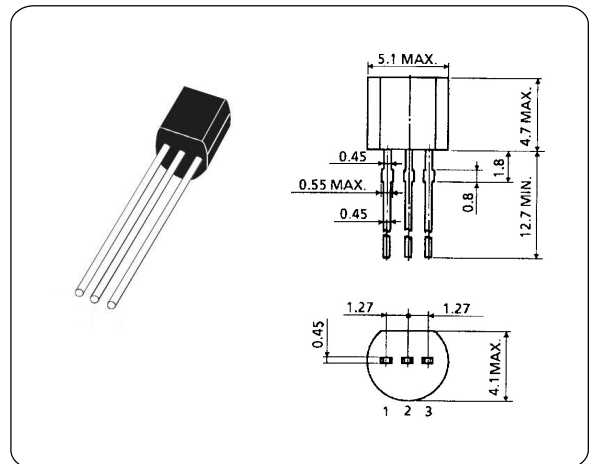
Silicon Bidirectional Triode Thyristors

STN1A60/80

GENERAL DESCRIPTION

Designed for use in solid state relays, MPU interface, TTL logic and any other light industrial or consumer application. Supplied in an inexpensive TO - 92 package which is readily adaptable for use in automatic insertion equipment.

Parameter	Symbol	Typ		Unit
		STN1A60	STN1A80	
Repetitive peak off-state voltages	V_{DRM} V_{RRM}	600	800	V
RMS on-state current	$I_{T(RMS)}$	1.0		A
Non-repetitive peak on-state current	I_{TSM}	10		A
Max. Operating Junction Temperature	T_j	110		°C
Storage Temperature	T_{stg}	-45~150		°C



Parameter	Symbol	Test Conditions	Min	Typ		Max	Unit
				STN1A60	STN1A80		
Repetitive peak off-state voltages	V_{DRM} V_{RRM}		—	600	800	—	V
RMS on-state current	$I_{T(RMS)}$	all conduction angles	—	1.0		—	A
On-state voltage	V_T	$I_T=1.5 A$	—	—		1.60	V
Holding current	I_H	$V_D = 12 V; I_{GT}=10 mA$	—	—		5	mA
Gate trigger current	T2+G+	I_{GT} $V_D = 6.0 V; R_L = 10 \Omega$	—	—		5.0	mA
	T2+G-		—	—		5.0	
	T2-G-		—	—		5.0	
	T2-G+		—	—		12	
Gate trigger voltage	V_{GT}	$V_D = 6.0 V; R_L = 10 \Omega$	—	0.5		1.8	V